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(54) **FEEDBACK BIASING FOR CASCODE AMPLIFIERS**

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(58) **Field of Classification Search** **330/310-311, 330/98, 133, 150, 302**
See application file for complete search history.

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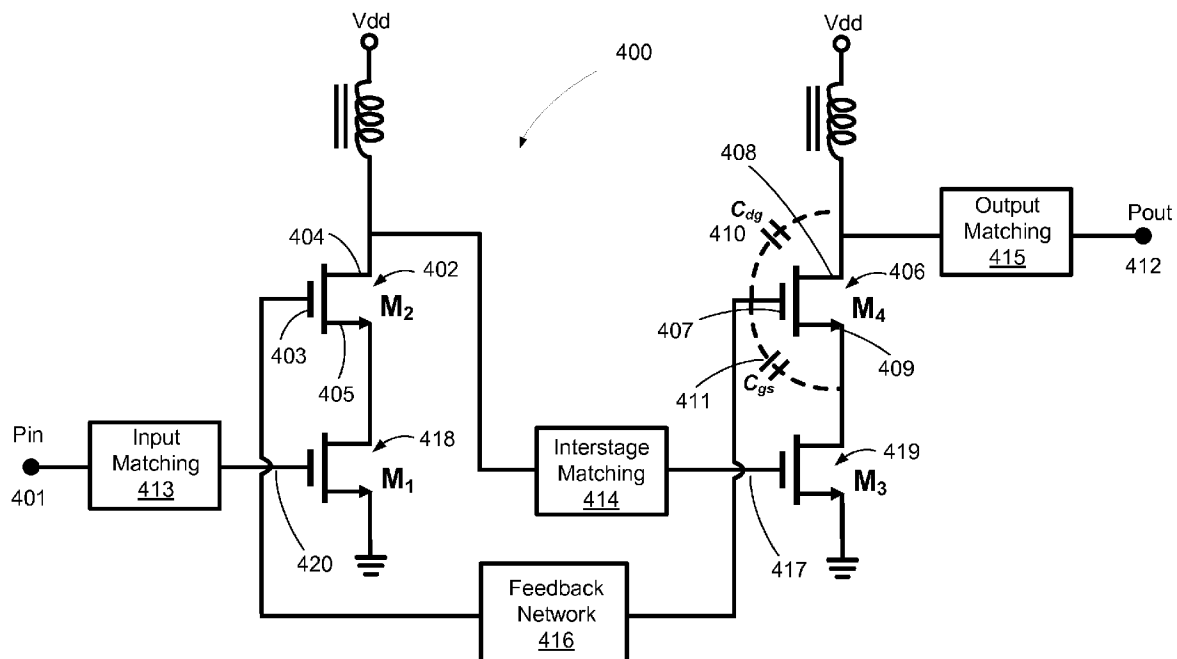
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(57) **ABSTRACT**

A system for a power transmitter may be provided. The system may include a first amplifier stage having at least a first transistor and a second transistor that are connected in a first cascode configuration; a second amplifier stage having at least a third transistor and a fourth transistor that are connected in a second cascode configuration, where the first transistor receives a system input of the power transmitter, where the second transistor is connected to the third transistor, and where the fourth transistor provides a system output of the power transmitter; and a feedback network that connects a first gate or base of the fourth transistor with a second gate or base of the second transistor.

20 Claims, 4 Drawing Sheets



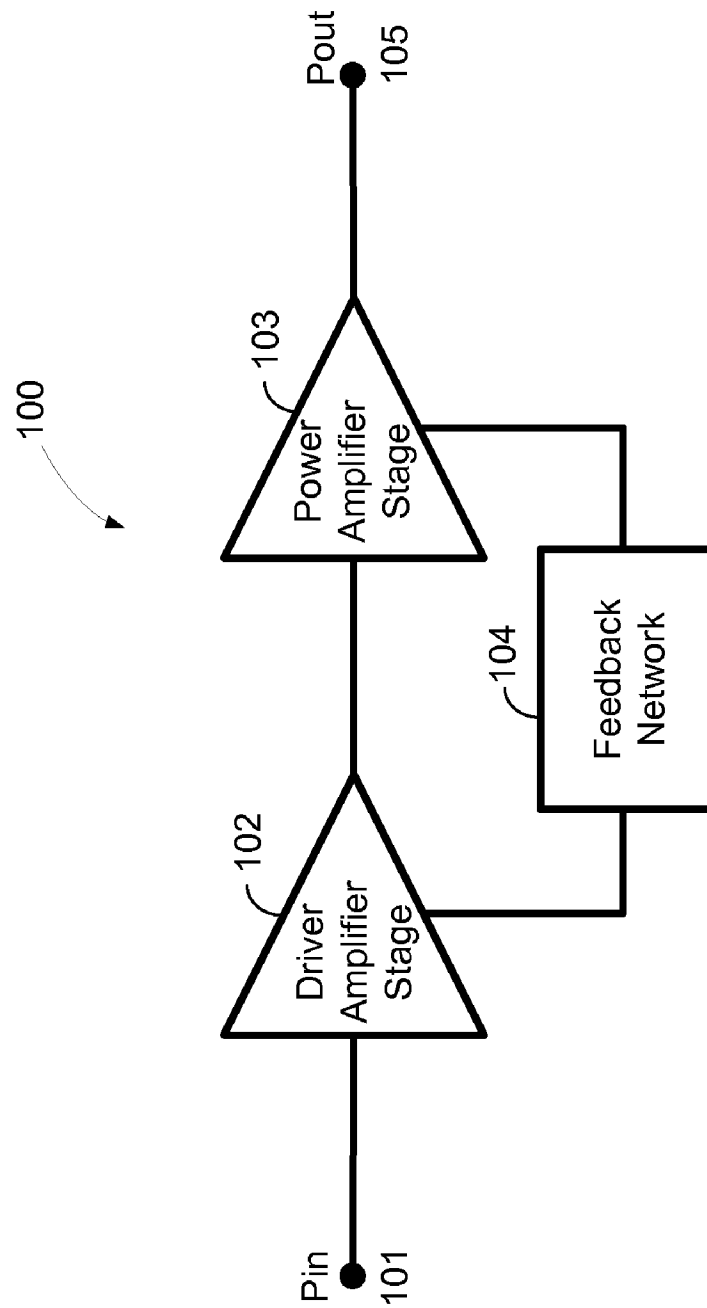


FIG. 1

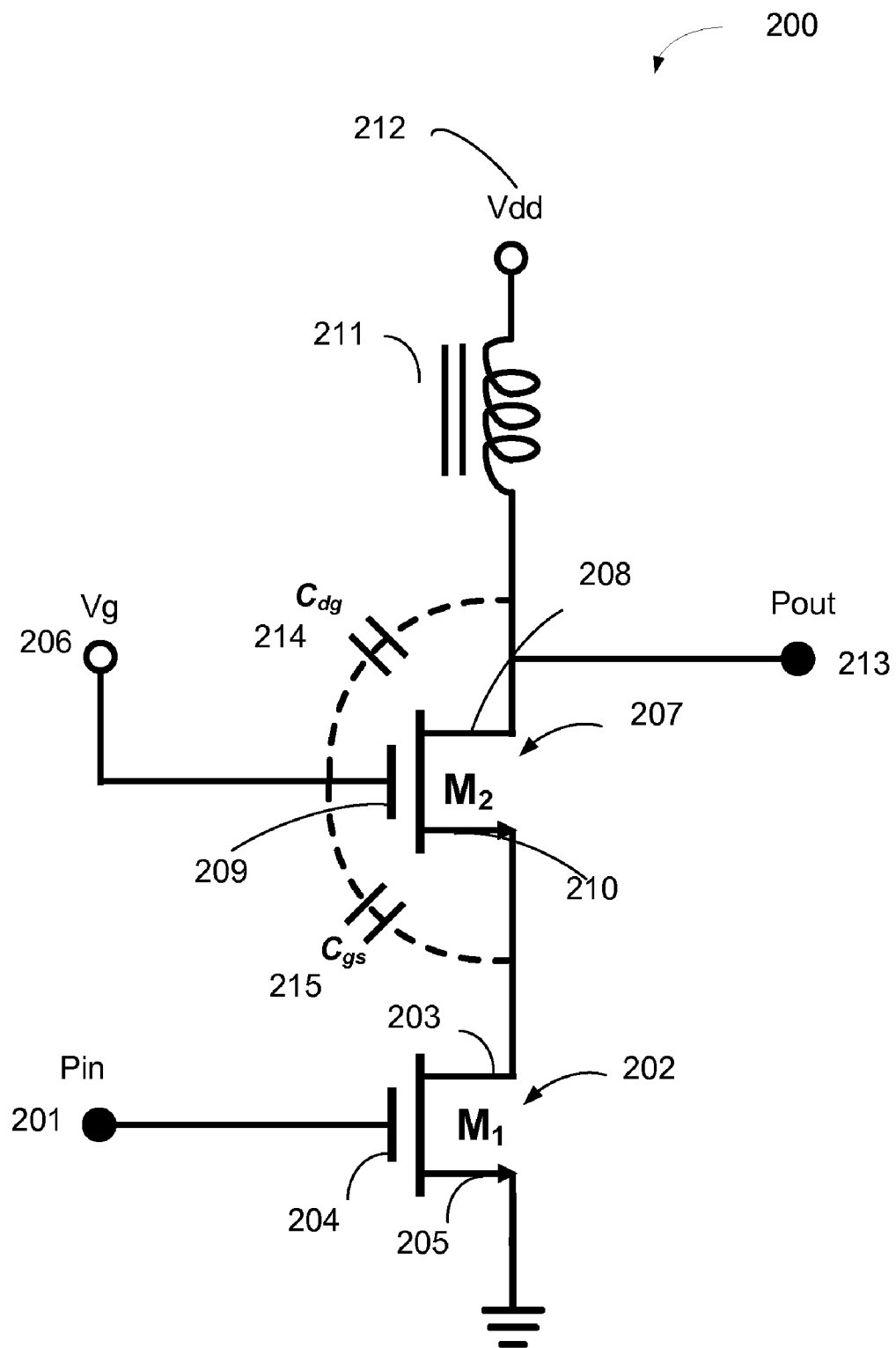


FIG. 2

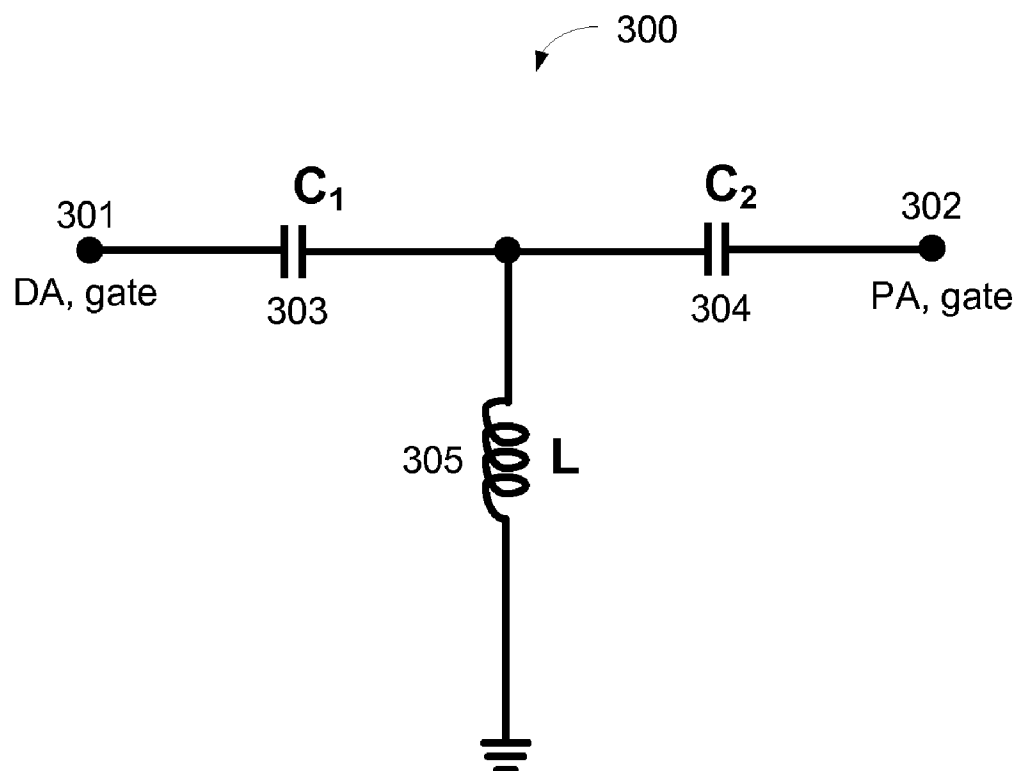


FIG. 3

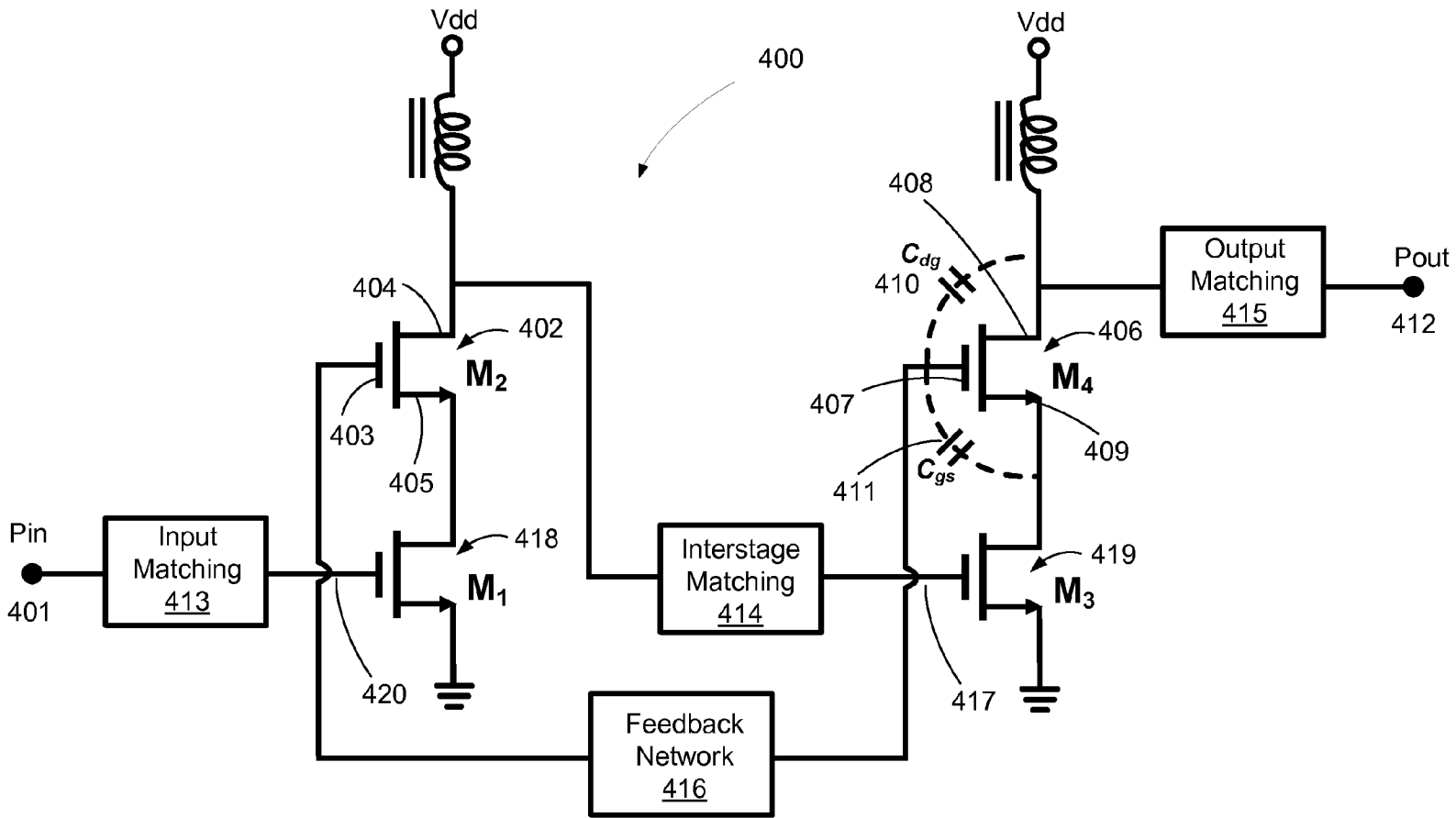


FIG. 4

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FEEDBACK BIASING FOR CASCODE AMPLIFIERS

FIELD OF INVENTION

Embodiments of the invention relate generally to cascode amplifiers, more particularly, to feedback biasing for cascode amplifiers in a power transmitter system.

BACKGROUND OF THE INVENTION

In complementary metal oxide semiconductor (CMOS) power amplifier design, there are two main issues: (1) voltage stress reduction for power amplifier's reliability and (2) linearity improvement. The voltage stress of a device can lead to oxide breakdown and hot carrier effects, and can increase the threshold voltage and degrade the performance of the device. Also, CMOS technology has an inherent linearity problem because of a number of parasitic capacitances. Accordingly, there is a need for feedback biasing for cascode amplifier.

BRIEF SUMMARY OF THE INVENTION

According to example embodiment of the invention, there is a system for a power transmitter. The system may include a first amplifier stage having at least a first transistor and a second transistor that are connected in a first cascode configuration; a second amplifier stage having at least a third transistor and a fourth transistor that are connected in a second cascode configuration, where the first transistor receives a system input of the power transmitter, where the second transistor is connected to the third transistor, and where the fourth transistor provides a system output of the power transmitter; and a feedback network that connects a first gate or base of the fourth transistor with a second gate or base of the second transistor.

According to another example embodiment of the invention, there is another system for a power transmitter. The system may include a first amplifier stage having at least a first transistor and a second transistor that are connected in a first cascode configuration; a second amplifier stage having at least a third transistor and a fourth transistor that are connected in a second cascode configuration, where the first transistor receives a system input of the power transmitter, where the second transistor is connected to the third transistor, and where the fourth transistor provides a system output of the power transmitter; and means for feeding one or more parasitic signals from a first gate or base of the fourth transistor as a feedback signal to a second gate or base of the second transistor.

BRIEF DESCRIPTION OF THE DRAWINGS

Having thus described the invention in general terms, reference will now be made to the accompanying drawings, which are not necessarily drawn to scale, and wherein:

FIG. 1 illustrates an example simplified power transmitter system that utilizes feedback biasing for cascode amplifiers, according to an example embodiment of the invention.

FIG. 2 illustrates a schematic diagram of a cascode amplifier system that illustrates parasitic capacitances of a common-gate transistor, according to an example embodiment of the invention.

FIG. 3 illustrates a schematic diagram for an example power transmitter system that utilizes feedback biasing for cascode amplifiers, according to an example embodiment of the invention.

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FIG. 4 illustrates an example schematic diagram of an example feedback network, according to an example embodiment of the invention.

DETAILED DESCRIPTION OF THE INVENTION

Example embodiments of the invention now will be described more fully hereinafter with reference to the accompanying drawings, in which some, but not all embodiments of the invention are shown. Indeed, these inventions may be embodied in many different forms and should not be construed as limited to the embodiments set forth herein; rather, these embodiments are provided so that this disclosure will satisfy applicable legal requirements. Like numbers refer to like elements throughout.

Embodiments of the invention may provide for a power transmitter system that may include a first cascode amplifier stage (e.g., a driver amplifier stage) and a second cascode amplifier stage (e.g., a power amplifier stage). In an example embodiment of the invention, the first cascode amplifier stage may include a first transistor configured as a common source amplifier, and a second transistor configured as a common gate amplifier. Likewise, the second cascode amplifier stage may include a third transistor configured as a common source amplifier, and a fourth transistor configured as a common gate amplifier. The power transmitter system may also include a feedback network that is connected between the gate of the common-gate amplifier in the first cascode amplifier stage and the gate of common-gate amplifier in the second cascode amplifier stage. The feedback network may be operative to provide parasitic signals from the gate of the common-gate amplifier in the second cascode amplifier stage as a feedback signal to the gate of the common-gate amplifier in the first cascode amplifier stage. The use of the feedback signal allows the power transmitter system to have less cutoff region and linear region while having more saturation region, thereby reducing operational variations of the power transmitter system. In other words, the operational cycle of the power transmitter system falls more into the saturation region and works less on the cutoff region compared to conventional power amplifiers. In addition, the use of the feedback signal allows the voltage of the common-gate amplifier in the first cascode amplifier stage to generally follow the output voltage of the power transmitter system (provided by the common-gate amplifier in the second cascode amplifier stage), thereby reducing the voltage stress of the common-gate amplifier in the first cascode amplifier stage.

It will be appreciated that example embodiments of the inventions may be illustratively described herein with respect to field effect transistors (FETs) having respective sources, gates, and drains. However, it will also be appreciated that other types of transistors may likewise be utilized instead of FETs, including bipolar junction transistors (BJTs) having respective emitters, bases and collectors. Thus, example sources, gates, and drains for FETs may correspond to respective emitters, bases, and collectors for BJTs. Likewise, common-source amplifiers utilizing FETs as described herein may be substituted with common-emitter amplifiers utilizing BJTs, according to an example embodiment of the invention. Similarly, common-gate amplifiers utilizing FETs as described herein may be substituted with common-base amplifiers utilizing BJTs, according to an example embodiment of the invention.

FIG. 1 illustrates an example simplified power transmitter system **100** that utilizes feedback biasing for cascode amplifiers, according to an example embodiment of the invention. As shown in FIG. 1, there may be a driver amplifier stage **102**,

a power amplifier stage **103**, and a feedback network **104**. According to an example embodiment of the invention, the driver amplifier stage **102** may receive a system **100** input such as a baseband signal or a radio frequency (RF) signal from the input port **101**, and may generate a first stage output to drive the power amplifier stage **103**. The power amplifier stage **103** may provide an amplified output signal to the output port **105**, which may provide the system **100** output.

As will be described herein, the driver amplifier stage **102** may include a first cascode amplifier stage, and the power amplifier stage **103** may include a second cascode amplifier stage. The first cascode amplifier stage may include a first transistor configured as a common source amplifier, and a second transistor configured as a common gate amplifier. Likewise, the second cascode amplifier stage may include a third transistor configured as a common source amplifier, and a fourth transistor configured as a common gate amplifier.

In FIG. 1, the feedback network **104** may feed back the common-gate parasitic signal of power amplifier stage **103** as a feedback signal to the common-gate of driver amplifier stage **102**, according to an example embodiment of the invention. The use of the feedback signal allows the power transmitter system **100** to have less cutoff region and linear region while having more saturation region, thereby reducing operational variations of the power transmitter system. In other words, the operational cycle of the power transmitter system **100** falls more into the saturation region and works less on the cutoff region compared to conventional power amplifiers. In addition, the use of the feedback signal allows the voltage of the common-gate amplifier in the driver amplifier stage **102** to generally follow the output voltage of the power transmitter system **100** (provided by the common-gate amplifier in the power amplifier stage **103**), thereby reducing the voltage stress of the common-gate amplifier in the driver amplifier stage, according to an example embodiment of the invention.

FIG. 2 illustrates a schematic diagram of a cascode amplifier system **200** that illustrates parasitic capacitances of a common-gate transistor, according to an example embodiment of the invention. It will be appreciated that the cascode amplifier system **200** may be utilized for the power amplifier stage **103** in FIG. 1, and similarly for the driver amplifier stage **102** in FIG. 1. In FIG. 2, the cascode amplifier system **200** may include a common-source device or transistor **202** (M_1) having a first source **205**, a first gate **204**, and a first drain **203**, according to an example embodiment of the invention. Likewise, the cascode power amplifier system **200** may also include a second common-gate transistor or device **207** (M_2) having a second source **210**, a second gate **209**, and a second drain **208**, according to an example embodiment of the invention.

According to an example embodiment of the invention, the first common-source device **202** (M_1) may be connected in series with the second common-gate device **207** (M_2) to reduce the voltage stress or burden that may otherwise be borne by a single device. According to an example embodiment of the invention, the devices **202** (M_1), **207** (M_2) may be connected in series by connecting the first drain **203** of the first common-source device **202** (M_1) to the second source **210** of the second common-gate device **207** (M_2). Further, the first source **205** of the first common-source device **202** (M_1) may be connected to ground (GND) while the second gate **209** of the second common-gate device **207** (M_2) may be connected to a gate bias port **206** (Vg). As will be described herein, the gate bias port **206** (Vg) may be connected to a feedback network. According to an example embodiment of the invention, an input port **201** (Pin) for cascode amplifier system **200** may be provided at the first gate **204** of the first

common-source device **202** (M_1). Likewise, an output port **213** (Pout) for the cascode amplifier system **200** may be provided at the second drain **208** of the second common-gate device **207** (M_2). According to an example embodiment of the invention, an RF choke **211** may also be provided between a DC voltage source or power supply **212** (Vdd) and the second drain **208**. The RF choke **211** may be operative to feed DC power to the second drain **208**.

During operation of the cascode amplifier system **200**, parasitic capacitances may be unavoidable. Thus, a drain-to-gate parasitic capacitance **214** (Cdg) may exist between a second drain **208** and a second gate **209** of the second common-gate device **207** (M_2), and a gate-to-source capacitance **411** (Cgs) may exist between the second gate **209** and the second source **210**. Accordingly, parasitic signals may be present at the second gate **209** based upon the parasitic capacitances **214** (Cdg) and **411** (Cgs) coupling to the respective second drain **408** and second source **409**.

FIG. 3 illustrates a schematic diagram for an example power transmitter system **300** that utilizes feedback biasing for cascode amplifiers, according to an example embodiment of the invention. It will be appreciated that the example power transmitter system **300** in FIG. 3 may be an example implementation of the simplified power transmitter system **100** in FIG. 1.

In FIG. 3, the power transmitter system **300** may include a first (e.g., driver) amplifier stage that includes a first common-source device or transistor **318** (M_1) and a second common-gate device transistor **302** (M_2) arranged in a cascode configuration. Likewise, the system **300** may include a second (e.g., power) amplifier stage that includes a third common-source device or transistor **319** (M_3) and a fourth common-gate device or transistor **306** (M_4) that is arranged in a cascode configuration.

The gate of the first common-source device or transistor **318** (M_1) may be connected to the input port **301** (Pin) via an input matching network **313**. The input matching network **313** may provide impedance matching to a prior stage. The input port **301** (Pin) may receive an analog (e.g., baseband) signal or an analog signal, according to an example embodiment of the invention. The amplified output signal of the first common-source device or transistor **318** (M_1) may be provided at the drain of the first common-source device or transistor **318** (M_1). Since the drain of the first common-source device or transistor **318** (M_1) is connected to the source **305**, the second common-gate device or transistor **302** (M_2) may receive the amplified output signal via the source **305**. The first stage output may be provided by the drain **304** of the second common-gate device or transistor **302** (M_2). An RF choke **350** may be operative to feed DC power from a DC voltage source Vdd or power supply to the drain **304**.

The first stage output from the drain **304** may be provided to the gate of the third common-source device or transistor **319** (M_3) of the second amplifier stage via an interstage matching network **314**. The interstage matching network **314** may provide impedance matching between the first amplifier stage and the second amplifier stage. The amplified output signal of the third common-source device or transistor **319** (M_3) may be provided at the drain of the third common-source device or transistor **319** (M_3). Since drain of the third common-source device or transistor **319** (M_3) is connected to the source **309** of the fourth common-gate device or transistor **306** (M_4), the fourth common-gate device or transistor **306** (M_4) may receive the amplified output signal via the source **309**. The drain **308** of the fourth common-gate device or transistor **306** (M_4) may be connected to the output port **312** (Pout) via an output matching block **315**. The output match-

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ing block **315** may provide impedance matching to a subsequent stage. In addition, an RF choke **352** may be operative to feed DC power from voltage source Vdd or power supply to the drain **308**.

In an example embodiment of the invention, a feedback network **316** may be used to provide feedback biasing using parasitic capacitances as well as to provide an AC virtual ground to the gates of the second common-gate device or transistor **302** (M_2) and the second common-gate device or transistor **306** (M_4). To do so, the feedback network **316** may connect the gate **307** of the fourth common-gate device or transistor **306** (M_4) with the gate **303** of the first common-source device or transistor **318** (M_1). The feedback network **316** may transfer parasitic signals at the gate **307** of the second common-gate device or transistor **306** (M_4) as a feedback signal to the gate **303** of the second common-gate device or transistor **302** (M_2) with appropriate phase, according to an example embodiment of the invention. Indeed, the phase of the feedback signal may provide for cancellation of at least a portion of the parasitic signals present at the gate **303** of the second common-gate device or transistor **302** (M_2). It will be appreciated that the parasitic signals may be present at the gate **307**, where the parasitic signals are transferred from the from one or both of (i) the source **309** of the second common-gate device **306** (M_4) by the parasitic gate-to-source capacitance **311** (C_{gs}) or (ii) the drain **308** of the second common-gate device **306** (M_4) by the drain-to-gate parasitic capacitance **310** (C_{dg}).

It will be appreciated that since the feedback network **316** is not connected to the signal path (e.g., any system input or output ports) of the power transmitter system **300**, the feedback provided by the feedback network **316** may have only a secondary impact on the performance of the power transmitter system **300**. It will be appreciated that the input matching block **313**, the interstage matching network **314**, and the output matching block **315** may be configured to provide for maximum power transfer from the input port **301** (Pin) to the output port **312** (Pout) for the power transmitter system **300**.

FIG. 4 illustrates an example schematic diagram **400** of an example feedback network, according to an example embodiment of the invention. The example feedback network of FIG. 4 may be utilized as an implementation of the feedback network **316** described with respect to FIG. 3, or the feedback network **104** described with respect to FIG. 1.

As shown in FIG. 4, the feedback network may include an inductor **405** (L) and two capacitors **403** (C_1) and **404** (C_2), which may be arranged in a T-configuration, according to an example embodiment of the invention. More specifically, a first end of the capacitor **403** (C_1) may be connected to the gate **303** of second common-gate device or transistor **302** (M_2) in the driver amplifier stage, while a second end of the capacitor **403** (C_1) may be connected to common node **406**. Likewise, a first end of the capacitor **404** (C_2) may be connected to the gate **307** of the second common-gate device or transistor **306** (M_4) in the power amplifier stage, while a second end of the capacitor **404** (C_2) may be connected to the common node **406**. The inductor **405** (L) may have a first end connected to the common node **406**, and a second end connected to ground (GND). It will be appreciated that while capacitors **403**, **404** and inductor **405** have been illustrated as individual components, they may likewise include multiple components without departing from example embodiments of the invention. For example, inductor **405** may actually include two or more inductors without departing from example embodiments of the invention.

Still referring to FIG. 4, it will be appreciated that the capacitors **403**, **404** in conjunction with the inductor **405** may

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provide a path for transferring parasitic signals at the gate **307** of the second common-gate device or transistor **306** (M_4) as a feedback signal to the gate **303** of the second common-gate device or transistor **302** (M_2) with appropriate phase, as described herein, according to an example embodiment of the invention. Likewise, the capacitors **403**, **404**, which are connected to the inductor **405** that is connected to ground, may provide an AC ground to the gates **303**, **307** of second common-gate device or transistor **302** (M_2) and the second common-gate device or transistor **306** (M_4).

Many modifications and other embodiments of the invention set forth herein will be apparent having the benefit of the teachings presented in the foregoing descriptions and the associated drawings. Therefore, it is to be understood that the invention is not to be limited to the specific embodiments disclosed and that modifications and other embodiments are intended to be included within the scope of the appended claims. Although specific terms are employed herein, they are used in a generic and descriptive sense only and not for purposes of limitation.

What is claimed is:

1. A system for a power transmitter, comprising:

a first amplifier stage having at least a first transistor and a second transistor that are connected in a first cascode configuration;

a second amplifier stage having at least a third transistor and a fourth transistor that are connected in a second cascode configuration, wherein the first transistor receives a system input of the power transmitter, wherein the second transistor is connected to the third transistor, and wherein the fourth transistor provides a system output of the power transmitter; and

a feedback network that connects a first gate or base of the fourth transistor with a second gate or base of the second transistor.

2. The system of claim 1, wherein the feedback network includes at least two capacitors and an inductor.

3. The system of claim 2, wherein the at least two capacitors includes a first capacitor and a second capacitor, wherein the first capacitor, the second capacitor, and the inductor each have a respective first end and a respective second end, wherein the first end of the first capacitor is connected to the first gate or base of the fourth transistor, wherein the second end is connected to a node that is commonly connected to the first end of the second capacitor and the first end of the inductor, wherein the second end of the second capacitor is connected to the second gate or base of the second transistor, wherein the second end of the inductor is connected to ground.

4. The system of claim 1, wherein the feedback network is operative to provide a feedback signal to the second gate or base of the second transistor, the feedback signal based upon one or more parasitic signals present at the first gate or base of the fourth transistor.

5. The system of claim 4, wherein the one or more parasitic signals are based upon at least one of (i) a drain-to-gate capacitance or (ii) a gate-to-source capacitance, associated with the fourth transistor.

6. The system of claim 4, wherein the feedback network is further operative to provide an AC ground for both of (i) the second gate or base of the second transistor and (ii) the first gate or base of the fourth transistor.

7. The system of claim 1, wherein the first transistor, the second transistor, the third transistor, and the fourth transistor comprise either (i) field effect transistors (FETs) having

respective gates, sources, and drains, or (ii) bipolar junction transistors (BJTs) having respective bases, emitters, and collectors.

8. The system of claim 1, wherein the first transistor and the third transistor are common source amplifiers or common emitter amplifiers, and wherein the second transistor and the fourth transistor are common gate amplifiers or common base amplifiers.

9. The system of claim 1,

wherein the first transistor includes a fourth gate or base and a first drain or collector, wherein the second transistor includes a second source or emitter, and a second drain or collector, wherein the third transistor includes a third gate or base, and a third drain or collector, and wherein the fourth transistor includes a fourth source or emitter, and a fourth drain or collector,

wherein the fourth gate or base receives the system input of the power transmitter, wherein the first drain or collector is connected to the second source or emitter, wherein the second drain or collector is connected to the third gate or base, wherein the third drain or collector is connected to the fourth source or emitter, and wherein the fourth drain or collector provides the system output of the power transmitter.

10. The system of claim 9, further comprising:

an interstage matching network that connects the second drain or collector to the third gate or base;

an input matching network that provides the system input to the fourth gate or base; and

an output matching network that receives the system output from the fourth drain or collector.

11. The system of claim 9,

wherein the first transistor further includes a first source or emitter that is connected to ground,

wherein the second drain or collector is further connected to a DC power supply,

wherein the third transistor further includes a third source or emitter that is connected to ground, and

wherein the fourth drain or collector is further connected to the DC power supply.

12. The system of claim 1, wherein the first amplifier stage is a driver amplifier stage, and wherein the second amplifier stage is a power amplifier stage.

13. A system for a power transmitter, comprising:

a first amplifier stage having at least a first transistor and a second transistor that are connected in a first cascode configuration;

a second amplifier stage having at least a third transistor and a fourth transistor that are connected in a second cascode configuration, wherein the first transistor receives a system input of the power transmitter, wherein the second transistor is connected to the third transistor, and wherein the fourth transistor provides a system output of the power transmitter; and

means for feeding one or more parasitic signals from a first gate or base of the fourth transistor as a feedback signal to a second gate or base of the second transistor.

14. The system of claim 13, wherein the one or more parasitic signals are based upon at least one of (i) a drain-to-gate capacitance or (ii) a gate-to-source capacitance, associated with the fourth transistor.

15. The system of claim 13, wherein the means is further operative to provide an AC ground for both of (i) the second gate or base of the second transistor and (ii) the first gate or base of the fourth transistor.

16. The system of claim 13, wherein the first transistor, the second transistor, the third transistor, and the fourth transistor comprise either (i) field effect transistors (FETs) having respective gates, sources, and drains, or (ii) bipolar junction transistors (BJTs) having respective bases, emitters, and collectors.

17. The system of claim 13, wherein the first transistor and the third transistor are common source amplifiers or common emitter amplifiers, and wherein the second transistor and the fourth transistor are common gate amplifiers or common base amplifiers.

18. The system of claim 13, wherein the first transistor includes a fourth gate or base and a first drain or collector, wherein the second transistor includes a second source or emitter, and a second drain or collector, wherein the third transistor includes a third gate or base, and a third drain or collector, and wherein the fourth transistor includes a fourth source or emitter, and a fourth drain or collector,

wherein the fourth gate or base receives the system input of the power transmitter, wherein the first drain or collector is connected to the second source or emitter, wherein the second drain or collector is connected to the third gate or base, wherein the third drain or collector is connected to the fourth source or emitter, and wherein the fourth drain or collector provides the system output of the power transmitter.

19. The system of claim 18, further comprising:

an interstage matching network that connects the second drain or collector to the third gate or base;

an input matching network that provides the system input to the fourth gate or base; and

an output matching network that receives the system output from the fourth drain or collector.

20. The system of claim 18, wherein the first transistor further includes a first source or emitter that is connected to ground,

wherein the second drain or collector is further connected to a DC power supply,

wherein the third transistor further includes a third source or emitter that is connected to ground, and

wherein the fourth drain or collector is further connected to the DC power supply.

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